TO-220F	N	MOS	N-CHANNEL MOSFET in a TO-220F Plastic Package.

Circu/ic-

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25)	2.0	A
Drain Current	I_D(Tc=100)	1.3	A
Drain Current - Pulsed	I_{DM}	6.0	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	120	mJ
Repetitive Avalanche Energy	E_{AR}	5.4	mJ
Avalanche Current	I_{AR}	2.0	A
Power Dissipation	P_D(Tc=25)	23	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	600			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V V_{GS}=0V			1.0	A
		V_{DS}=480V T_C=125			100	A
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}=±30V V_{DS}=0V			±0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250 A	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=1.0A		4.0	5.0	
Forward Transconductance	g_{FS}	V_{DS}=40V I_D=1.0A		2.05		S
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=2.0A			1.4	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		320	420	pF
Output Capacitance	C_{oss}			35	46	pF
Reverse Transfer Capacitance	C_{rss}			4.5	6.0	pF
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=300V I_D=2.0A R_G=25		8.0	30	ns
Turn-On Rise Time	t_r			23	60	ns
Turn-Off Delay Time	$t_{d(off)}$					

/ Package Dimensions

